



EXPRESS MAIL NO. EL897863842US

PATENT

#8/c  
up  
1/16/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Robert Louis Hodges  
Application No. : 09/733,243 ✓  
Filed : December 7, 2000  
For : SELF-ALIGNED GATE AND METHOD

Examiner : Michael Manh Trinh  
Art Unit : 2822  
Docket No. : 98-P-104C1 (850063.542C1)  
Date : January 3, 2003

RECEIVED  
JAN - 8 2003  
TECHNOLOGY CENTER 2800

Commissioner for Patents  
Washington, DC 20231

AMENDMENT

Commissioner for Patents:

In response to the Office Action dated July 3, 2002, please extend the period of time for response three (3) months, to expire on January 3, 2003. Enclosed are a Petition for an Extension of Time and the requisite fee. Please amend the application as follows:

In the Specification:

Please replace the paragraph beginning at line 16, page 5, with the following rewritten paragraph:

C1  
In a step 46, a second layer 48 is formed on the first layer 44. The second layer 48 is formed from a material that is chemically different than the first layer 44. As a result, the second layer 48 may be etched by an etching process that does not etch the first layer 44. The shallow trench isolation structures 39 are protected from etching processes that could damage or affect them by chemical selectivity with respect to the second layer 48, *i.e.*, etching processes for